

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): A composite for forming a ferroelectric thin film made of a colloidal solution applicable to the metal organic deposition method containing an organometallic compound including metal constituting a ferroelectric thin film, comprising:

at least water other than water of crystallization in the organometallic compound.

2. (original): The composite for forming a ferroelectric thin film according to claim 1, wherein molar quantity of the water other than the water of crystallization in the organometallic compound is 1 to 10 times as much as total molar quantity of the metal contained in the colloidal solution.

3. (original): The composite for forming a ferroelectric thin film according to claim 2, wherein the molar quantity of the water other than the water of crystallization in the organometallic compound is 5 to 7 times as much as the total molar quantity of the metal contained in the colloidal solution.

4. (currently amended): A ferroelectric thin film made of the composite for forming a ferroelectric thin film according to claim 1, ~~any one of claims 1 to 3.~~

5. (original): A liquid-jet head comprising:

a piezoelectric element including the ferroelectric thin film according to claim 4 as a piezoelectric actuator that ejects a liquid.

6. (original): A method of manufacturing a ferroelectric thin film comprising:

adding water other than water of crystallization in an organometallic compound to a colloidal solution applicable to the metal organic deposition method containing the organometallic compound including metal constituting a ferroelectric thin film;

coating the obtained composite for forming a ferroelectric thin film on a target object;
and

forming the ferroelectric thin film by drying and sintering the composite for forming a ferroelectric thin film on the target object.

7. (original): The method of manufacturing a ferroelectric thin film according to claim 6,

wherein the composite for forming a ferroelectric thin film is conveyed to a nozzle connected to a tank pooling the composite for forming a ferroelectric thin film by introducing dry inert gas into the tank, and the composite for forming a ferroelectric thin film is dropped onto the rotating target object from the nozzle when coating the composite for forming a ferroelectric thin film on the target object.

8. (previously presented): The method of manufacturing a ferroelectric thin film according to claim 6,

wherein the water other than the water of crystallization is added after addition of a hydrolysis inhibitor to the colloidal solution.